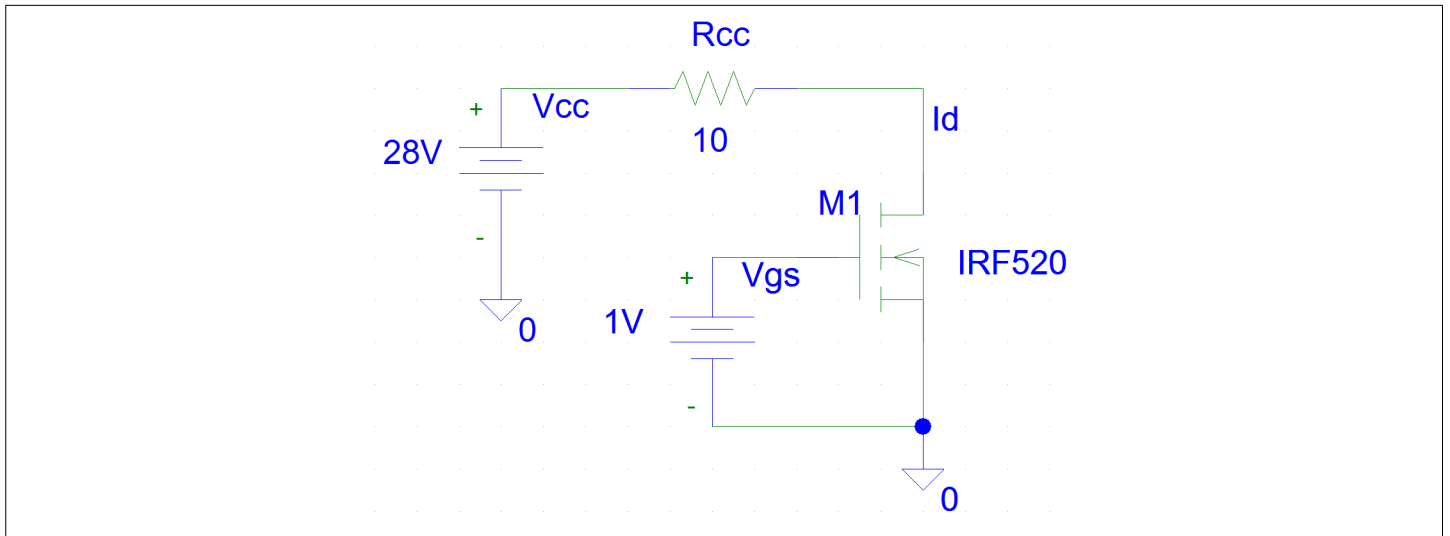


Simulation of class AB RF Power amplifier

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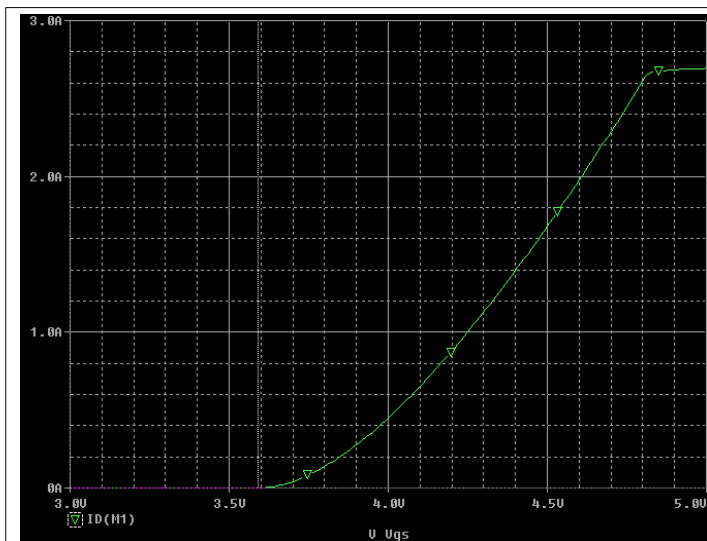
In this exercise, we analyze the operation of a class AB RF power amplifier RF. The power MOSFET IRF520A is used as active device. In particular, we want to realize an amplifier at 10MHz with an output power $P_o = 20W$ and standard in / out impedances of 50Ω . The supply voltage is set to 28V.



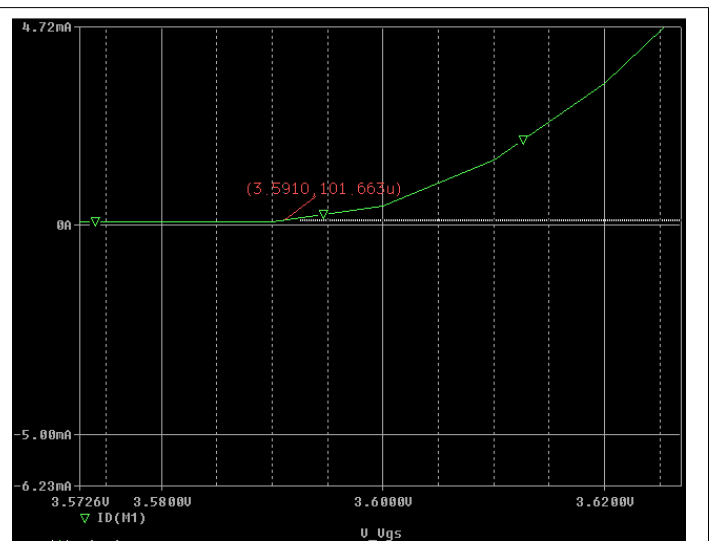
POINT 1 – The transfer static characteristic

In order to determine the transfer characteristic of the active device, draw the circuit shown in Fig. 1. Insert a MbreakN3 from the library of the simulator using the parameters available on Google Classroom website for the MOSFET IRF520A.

Perform a static analysis by varying the gate-source voltage between 3V and 5V with 0.01V step. Draw the drain current as a function of the voltage V_{gs} . Measure the device threshold voltage. (identify the voltage when the drain current is 100uA)



transfer characteristic of the active device



$I_d=100\mu A$ when $V_{gs}=3,59V$

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POINT 2 – The measurement of input and output MOSFET impedances

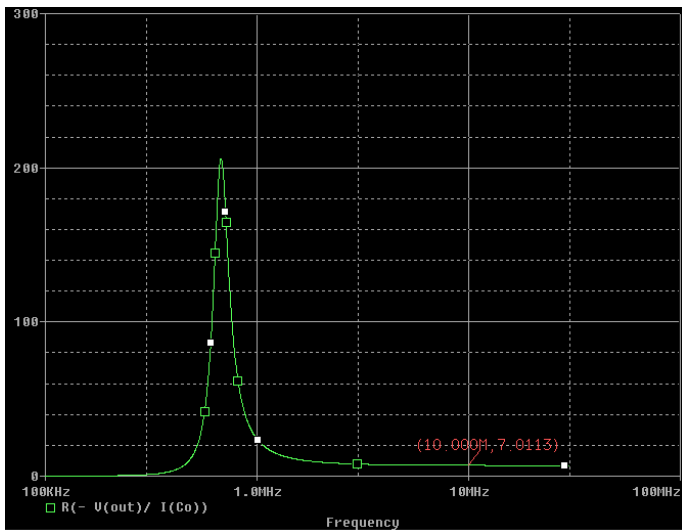
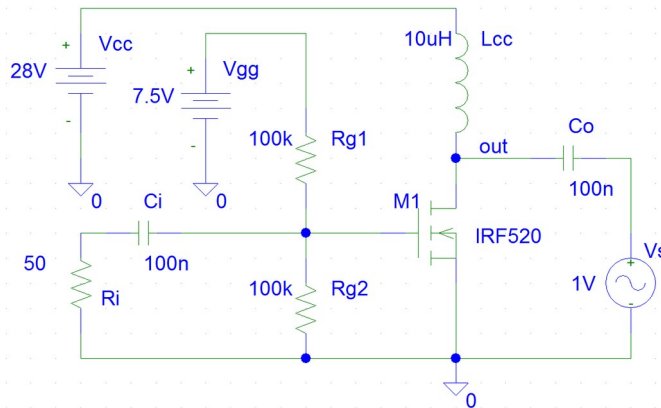
The common source class AB amplifier to be studied is shown in Fig. 2. A blocking inductance is inserted on the drain. The gate bias is realized by the battery V_{gg} and the voltage divider R_{g1} and R_{g2} . Set the voltage their values in order to have a quiescent current I_{d0} of 80mA (use the results of the previous step).

From transfer characteristic $I_D = 80\text{ mA}$ when $V_{GS} = 3,75\text{ V}$

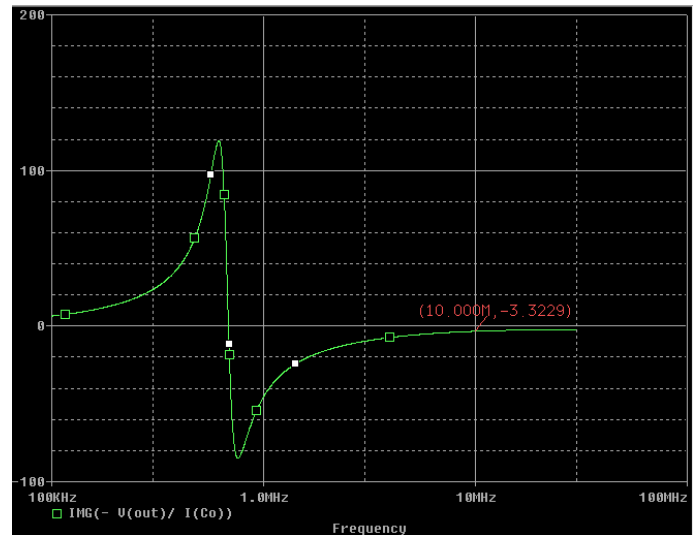
$$V_{GS} = \frac{R_{G2} V_{GG}}{R_{G1} + R_{G2}} \rightarrow V_{GG} = \frac{(R_{G1} + R_{G2}) V_{GS}}{R_{G2}} = 2 V_{GS} = 7,5\text{ V}$$

POINT 2A

Close the input port on a 50Ω . Use an AC analysis ($V_s = 1\text{V}$ - large signal) to evaluate the real and imaginary parts of the output impedance of the active device at the frequency of interest.



Real part of output impedance at 10MHz = 7,0113



Imaginary part of output impedance at 10MHz = -3,3229

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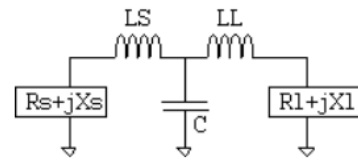
With obtained values, realize a 3 elements output matching network in order to adapt for maximum power transfer.

Source Resistance: Source Reactance:

Load Resistance: Load Reactance:

Desired Q: Frequency:

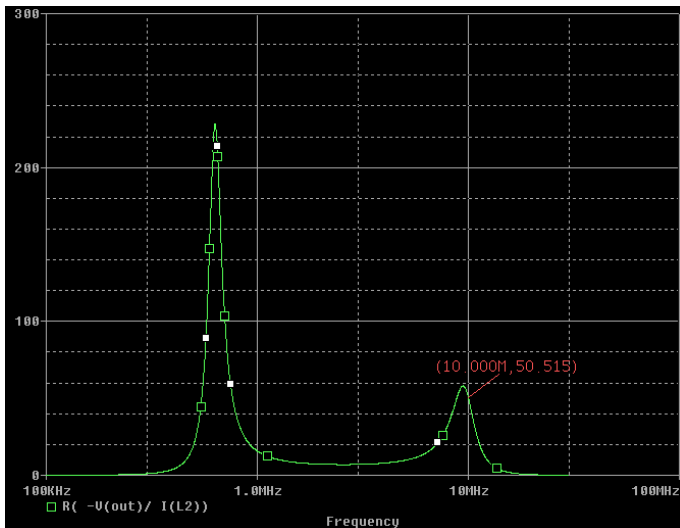
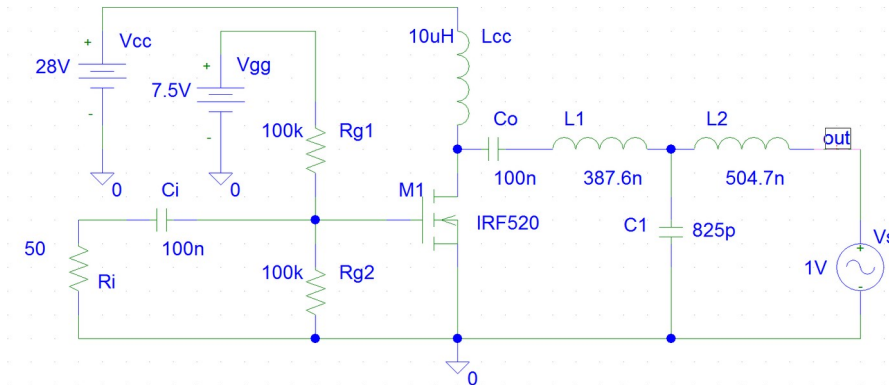
LOWPASS T MATCHING NETWORK



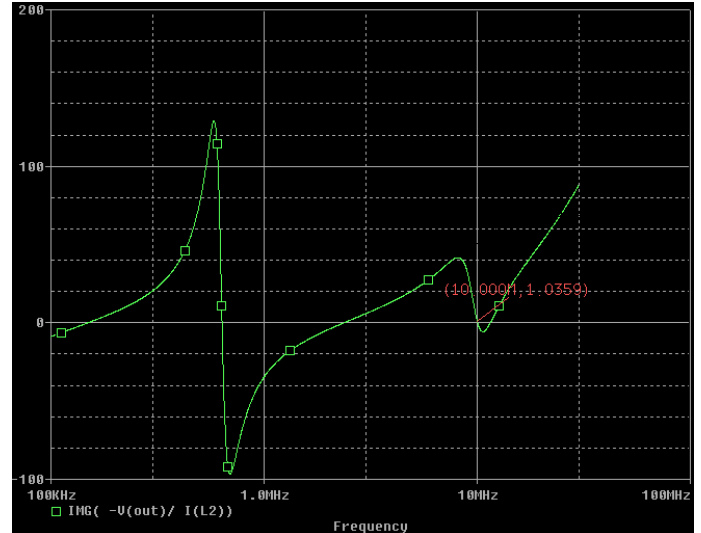
C Value: pF

LS Value: nH

LL Value: nH



Real part of output impedance at 10MHz = 50,515 ohm



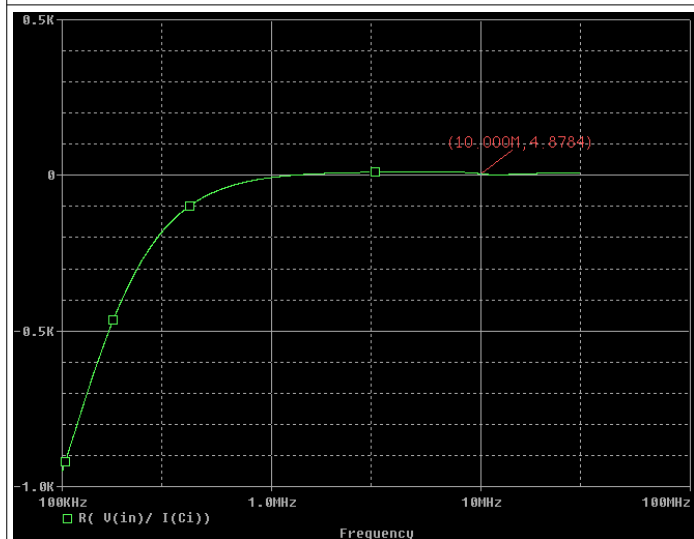
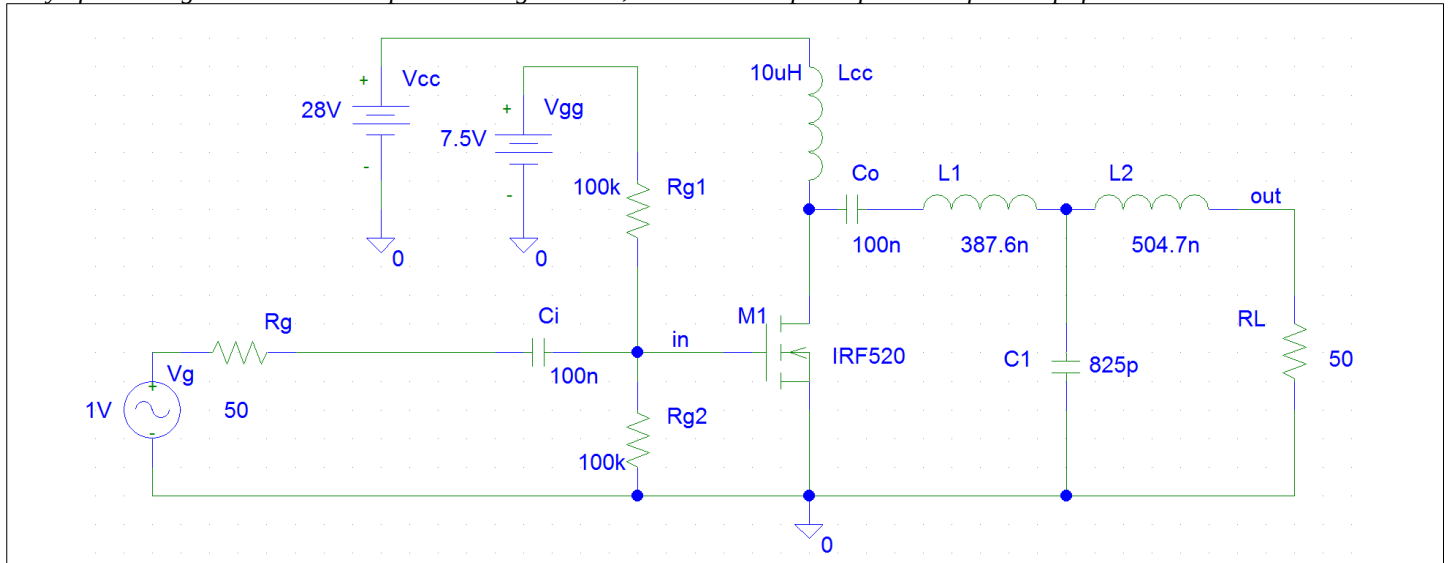
Imaginary part of output impedance at 10MHz = 1

Simulation of class AB RF Power amplifier

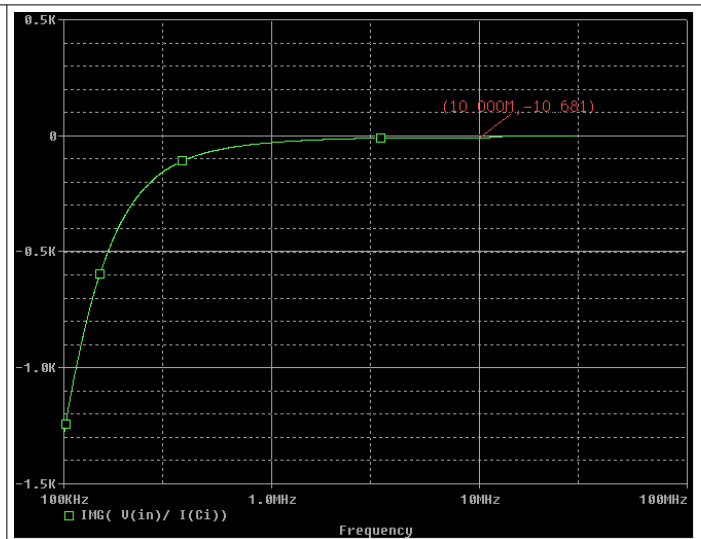
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POINT 2B

Only after having connected the output matching network, measure the input impedance of the amplifier.



Real part of input impedance at 10MHz = 4,8784 ohm



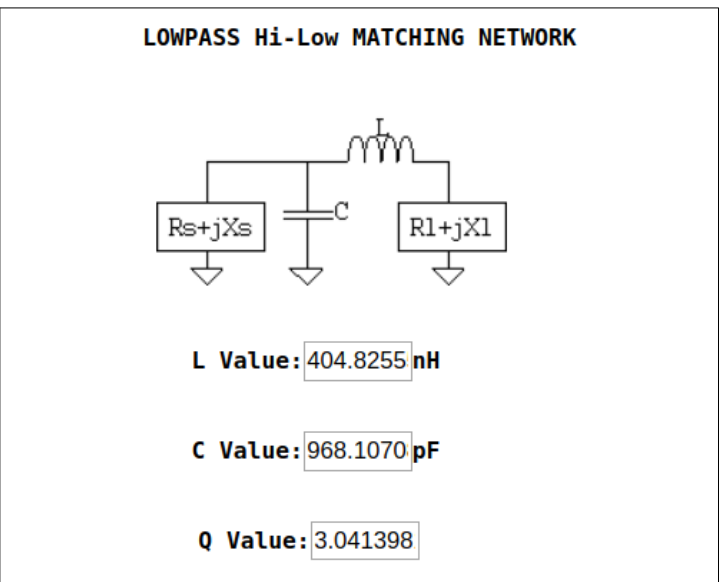
Imaginary part of output impedance at 10MHz = -10,681

Design the corresponding 2-elements matching network.

Source Resistance: Source Reactance:

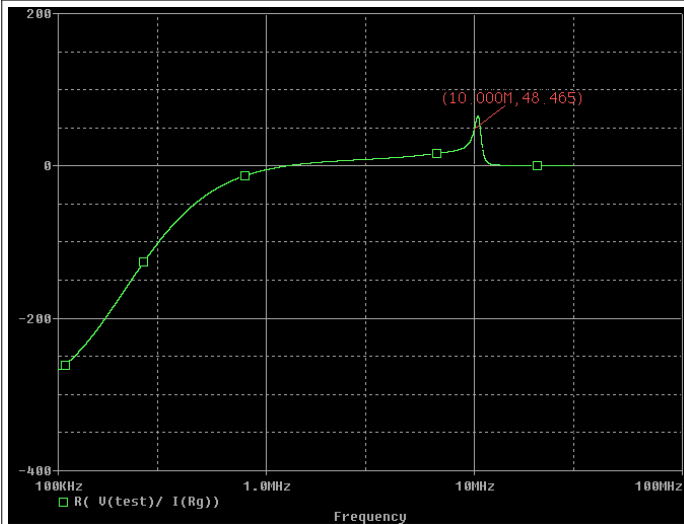
Load Resistance: Load Reactance:

Desired Q: Frequency:

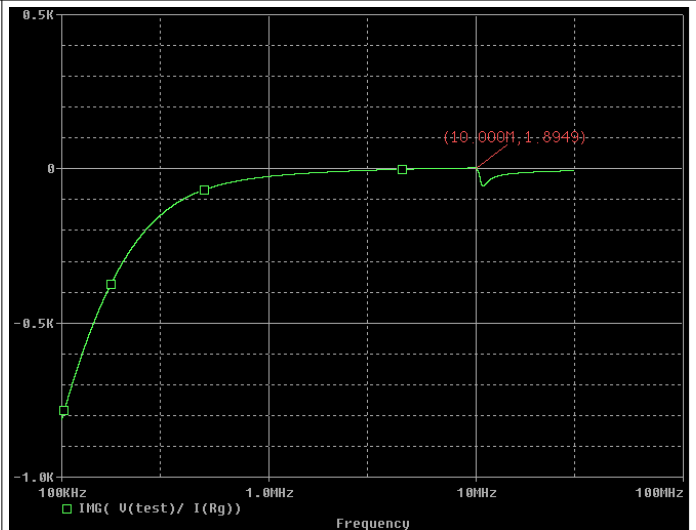


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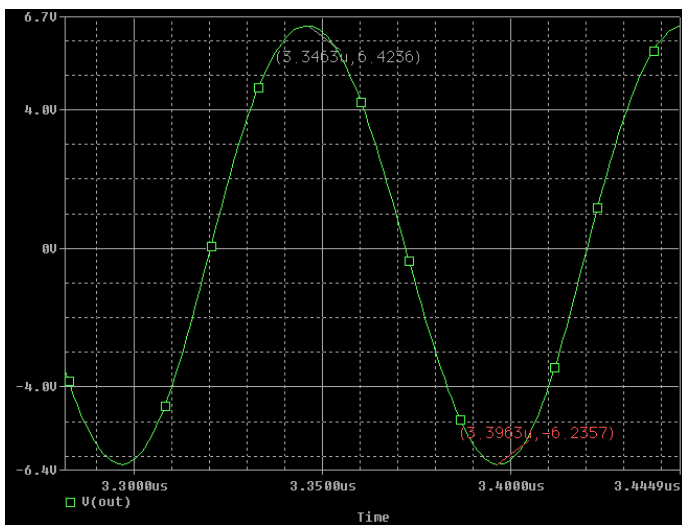
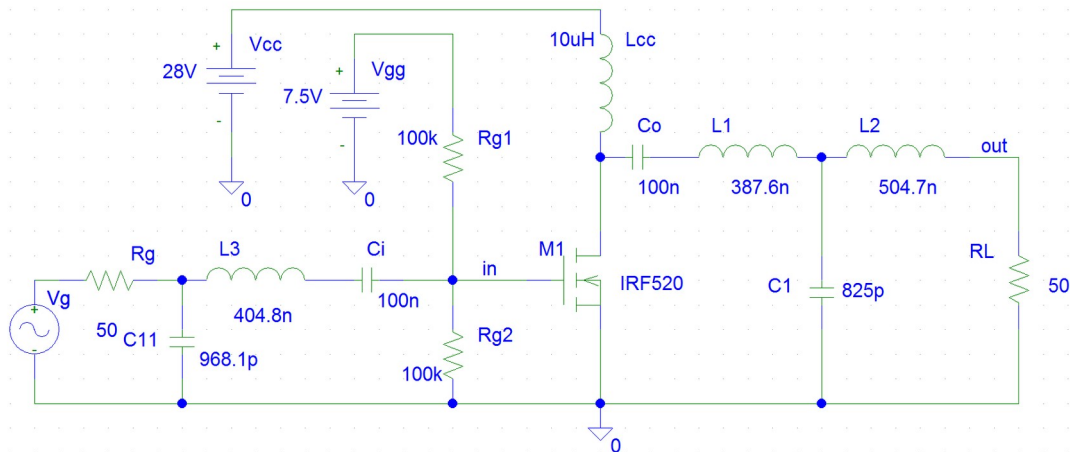
Real part of input impedance at 10MHz = 48 ohm



Imaginary part of output impedance at 10MHz = 1

POINT 3 – The verification of Amplifier Performances

Using the designed circuit, set an input sinusoidal signal V_g with amplitude of 1V and frequency 10MHz. Calculate the power gain by measuring output and input power. In order to measure the output power, measure the amplitude V_{pp} at output and calculate the power supplied to the load according to the relation $P_o = V_{PP}^2 / 8R_L$.



$$P_o = \frac{V_{PP}^2}{8R_L}$$

$$R_L = 50 \Omega$$

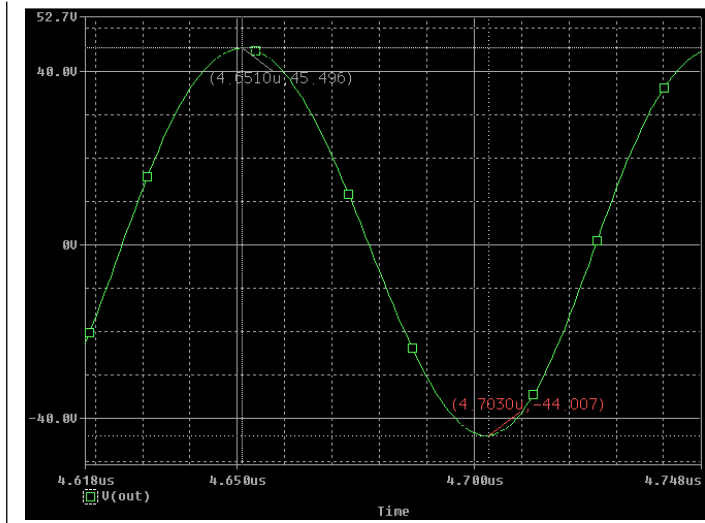
from simulation $V_{PP} = 12,66 V$ with $V_G = 1 V$

$$P_o \approx 0,4 W$$

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Increase the amplitude of the input signal to obtain an output power of about 20W.



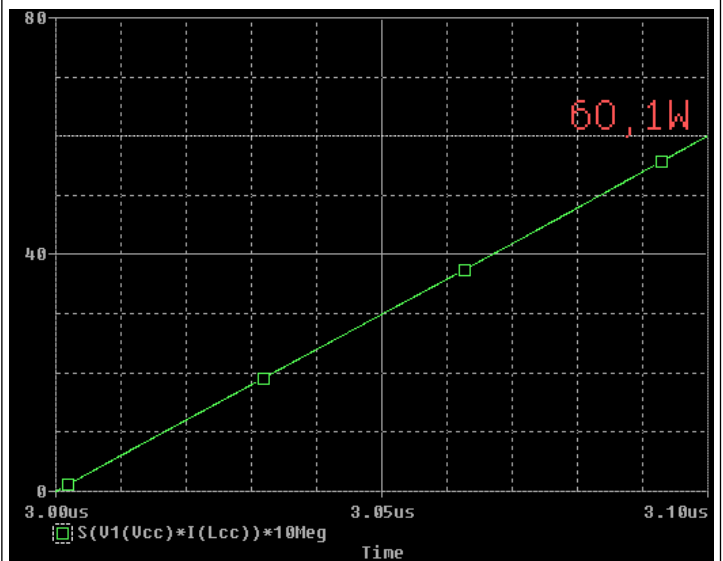
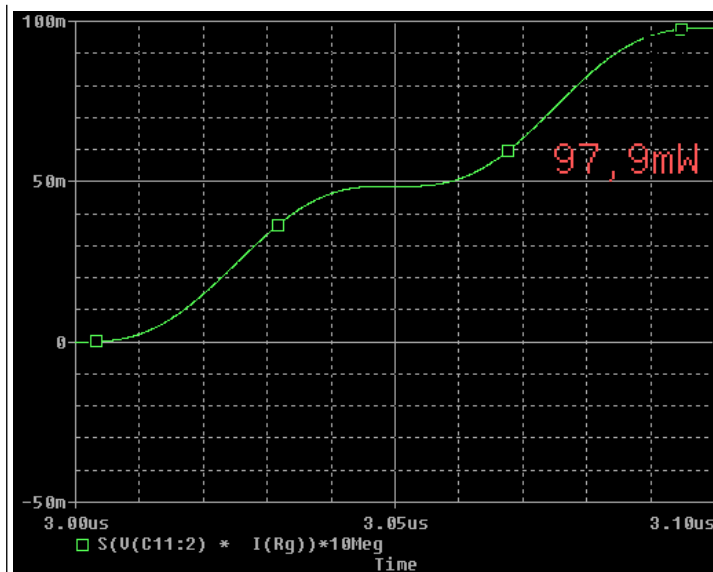
$$P_O = \frac{V_{PP}^2}{8 R_L}$$

$$R_L = 50 \Omega$$

from simulation $V_{PP} = 89,5 V$ with $V_G = 6,3 V$

$$P_O \approx 20,02 W$$

To calculate the input power supplied to the amplifier, evaluate the integral of the product $VC11 * IRG$ in one signal period (Pspice expression, $S(VC11 * IRG) * 10Meg$). In a similar way, evaluate the power supplied by power supply Vcc and calculate the efficiency of the amplifier at nominal power.



$$\eta = \frac{P_{OUT}}{P_{DD}} = \frac{20,02}{60,07} W \approx 33,3 \%$$

$$P_{IN} + P_{DD} = P_{OUT} + P_{DISS} \rightarrow P_{DISS} = P_{IN} + P_{DD} - P_{OUT} = 0,097 W + 60,07 W - 20,02 W \approx 40,15 W$$